Physics

(Chapter 14)(Semiconductor Electronics: Materials, Devices and Simple Circuits)
(Class 12)

Exercises

Question 14.1:
In an n-type silicon, which of the following statement is true:

(a) Electrons are majority carriers and trivalent atoms are the dopants.

(b) Electrons are minority carriers and pentavalent atoms are the dopants.

(c) Holes are minority carriers and pentavalent atoms are the dopants.

(d) Holes are majority carriers and trivalent atoms are the dopants.

Answer 14.1:
The correct statement is (c).
In an n-type silicon, the electrons are the majority carriers, while the holes are the minority carriers. An n-type semiconductor is obtained when pentavalent atoms, such as phosphorus, are doped in silicon atoms.

Question 14.2:
Which of the statements given in Exercise 14.1 is true for p-type semiconductors.

Answer 14.2:
The correct statement is (d).
In a p-type semiconductor, the holes are the majority carriers, while the electrons are the minority carriers. A p-type semiconductor is obtained when trivalent atoms, such as aluminium, are doped in silicon atoms.

Question 14.3:
Carbon, silicon and germanium have four valence electrons each. These are characterised by valence and conduction bands separated by energy band gap respectively equal to $(E_g)_C$, $(E_g)_{Si}$ and $(E_g)_{Ge}$. Which of the following statements is true?

(a) $(E_g)_{Si} < (E_g)_{Ge} < (E_g)_C$

(b) $(E_g)_C < (E_g)_{Ge} > (E_g)_{Si}$

(c) $(E_g)_C > (E_g)_{Si} > (E_g)_{Ge}$

(d) $(E_g)_C = (E_g)_{Si} = (E_g)_{Ge}$

Answer 14.3:
The correct statement is (c).
Of the three given elements, the energy band gap of carbon is the maximum and that of germanium is the least.
The energy band gap of these elements are related as: $(E_g)_C > (E_g)_{Si} > (E_g)_{Ge}$.

Question 14.4:
In an unbiased p-n junction, holes diffuse from the p-region to n-region because

(a) free electrons in the n-region attract them.

(b) they move across the junction by the potential difference.

(c) hole concentration in p-region is more as compared to n-region.

(d) All the above.

Answer 14.4:

The correct statement is (c).

The diffusion of charge carriers across a junction takes place from the region of higher concentration to the region of lower concentration. In this case, the p-region has greater concentration of holes than the n-region. Hence, in an unbiased p-n junction, holes diffuse from the p-region to the n-region.

Question 14.5:

When a forward bias is applied to a p-n junction, it

(a) raises the potential barrier.

(b) reduces the majority carrier current to zero.

(c) lowers the potential barrier.

(d) None of the above.

Answer 14.5:

The correct statement is (c).

When a forward bias is applied to a p-n junction, it lowers the value of potential barrier. In the case of a forward bias, the potential barrier opposes the applied voltage. Hence, the potential barrier across the junction gets reduced.

Question 14.6:

In half-wave rectification, what is the output frequency if the input frequency is 50 Hz. What is the output frequency of a full-wave rectifier for the same input frequency?

Answer 14.6:

Input frequency = 50 Hz

For a half-wave rectifier, the output frequency is equal to the input frequency.

$\therefore$ Output frequency = 50 Hz

For a full-wave rectifier, the output frequency is twice the input frequency.

$\therefore$ Output frequency = $2 \times 50 = 100$ Hz